

B' said supplemental substrate is constructed from a material having a substantially similar coefficient of thermal expansion as that of said primary substrate so that the presence of the supplemental substrate prevents the semiconductor chip carrier from warping.

10. (Unamended) A semiconductor chip carrier according to claim 9, wherein said supplemental substrate is constructed from a same material as said primary substrate.

11. (Unamended) A semiconductor chip carrier according to claim 9, wherein said primary substrate is constructed from a material selected from one of Bis-maleimide triazine epoxy, FR4, polyimide, and polytetrafluoroethylene.

B' 12. (Unamended) A semiconductor chip carrier according to claim 9, wherein said chip carrier is a ball-grid array chip carrier.

13. (Unamended) A semiconductor chip carrier according to claim 9, wherein said metal heat sink plate consists of a metal selected from one of Cu, Cu-W, Al, and alloys thereof.

14. (Unamended) A semiconductor chip carrier according to claim 9, wherein said supplemental substrate has a Cu-Ni finish layer.

15. (Unamended) A semiconductor chip carrier according to claim 9, wherein said supplemental substrate has a cavity exposing a portion of said metal heat sink plate.

20. (Unamended) A semiconductor chip carrier according to claim 9, wherein said primary substrate comprises a hole forming a die-attach cavity wherein the semiconductor chip is attached to the first side of the metal heat sink plate within the die-attach cavity.

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